**Product data sheet** 

## 1. General description

Dual ultrafast power diode in a SOT429 (3-lead TO-247) plastic package.

### 2. Features and benefits

- · Very low on-state loss
- Fast switching
- · Soft recovery characteristic minimizes power consuming oscillations
- · High reverse surge capability
- · High thermal cycling performance
- Low thermal resistance

### 3. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	200	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 113 °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3	-	-	15	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	-	170	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	-	185	Α
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	0.95	1.05	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1	1.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.78	0.9	V
Dynamic ch	aracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/µs}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	20	28	ns

# 4. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		A1   A2
2	K	cathode		A1
3	A2	anode 2		K sym125
mb	К	mounting base; cathode		
			TO-247 (SOT429)	

# 5. Ordering information

**Table 3. Ordering information** 

Type number	Package							
	Name	Description	Version					
BYV72EW-200	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429					

# 6. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	200	V
$V_{RWM}$	crest working reverse voltage		-	200	V
$V_R$	reverse voltage	DC; T <sub>mb</sub> ≤ 144 °C	-	200	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 113 °C; square-wave pulse; per diode; Fig. 1; Fig. 2; Fig. 3	-	15	Α
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 104 °C; square-wave pulse; both diodes conducting	-	30	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	-	170	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	185	Α
I <sub>RRM</sub>	repetitive peak reverse current	$\delta$ = 0.001; $t_p$ = 2 $\mu$ s; per diode	-	0.2	Α
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs; per diode	-	0.2	Α
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	150	°C
Electrostation	c discharge				
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ	-	8	kV

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#### **Dual ultrafast power diode**

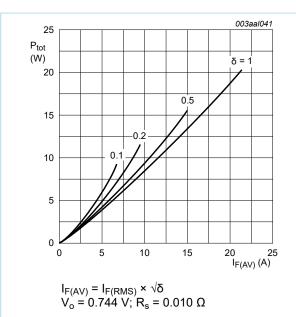


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; per diode; maximum values

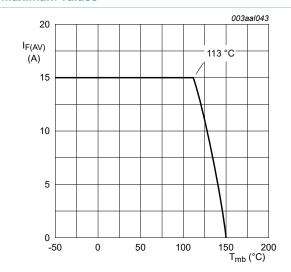


Fig. 3. Average forward current as a function of mounting base temperature; per diode; maximum values

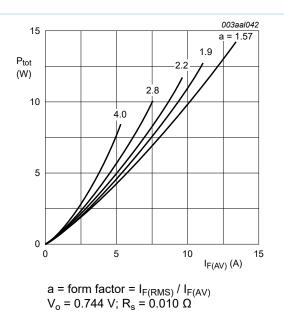


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; per diode; maximum values

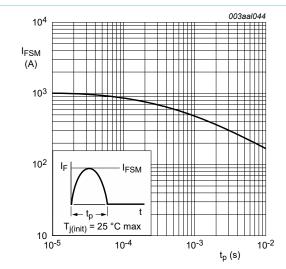


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; per diode; maximum values

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**Dual ultrafast power diode** 

### 7. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	2.4	K/W
	mounting base	with heatsink compound; both diodes conducting	-	-	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

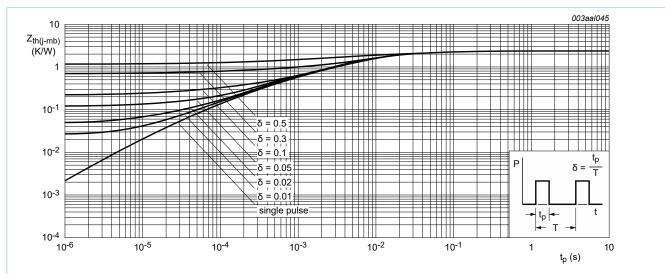


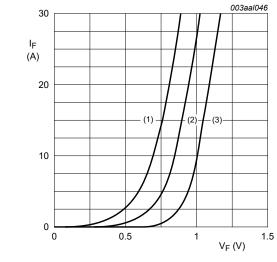
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width; per diode; maximum values

### 8. Characteristics

#### **Table 6. Characteristics**

characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics			·		
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	0.95	1.05	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1	1.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.78	0.9	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	10	100	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C	-	0.5	1	mA
Dynamic cl	haracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	20	28	ns
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 20 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	6	15	nC
$V_{FR}$	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A}/\mu\text{s}; T_j = 25 °C;$ Fig. 8	-	1	-	V



(3) T<sub>i</sub> = 25 °C; maximum values

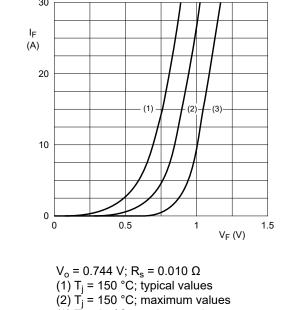


Fig. 6. Forward current as a function of forward voltage; per diode

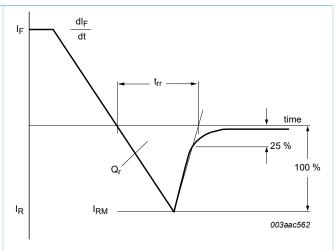
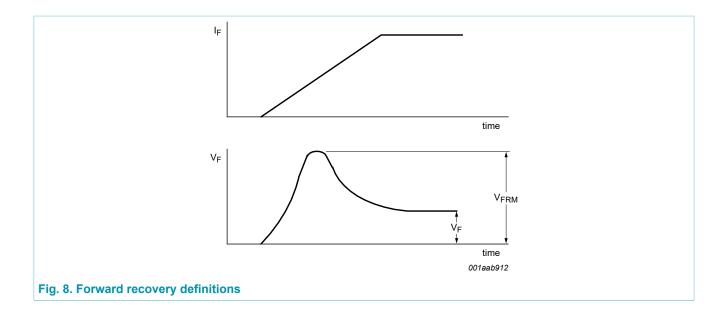


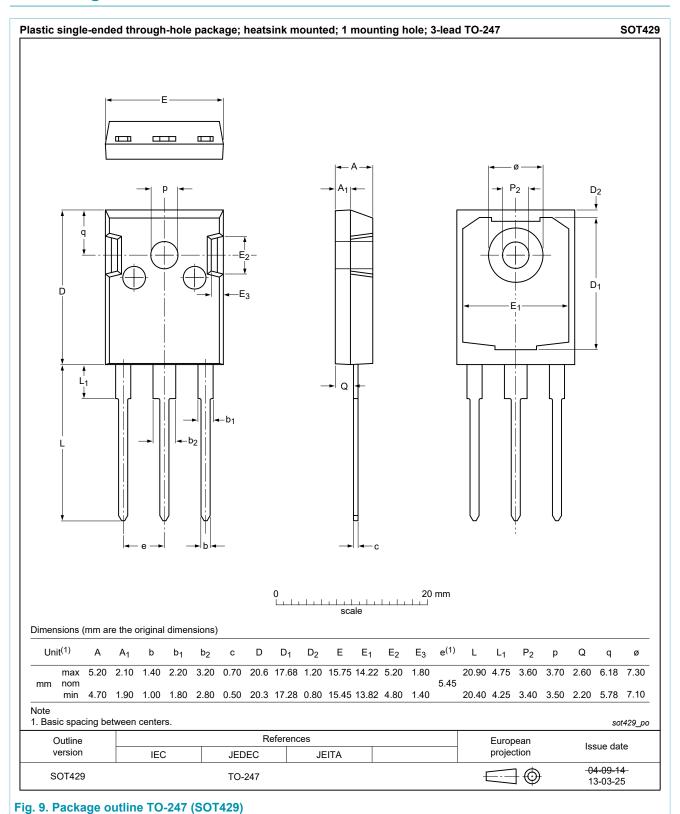
Fig. 7. Reverse recovery definitions; ramp recovery

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### **Dual ultrafast power diode**



# 9. Package outline



### 10. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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# **BYV72EW-200**

**Dual ultrafast power diode** 

### 11. Contents

1.	General description	1
2.	Features and benefits	1
3.	Quick reference data	1
4.	Pinning information	2
5.	Ordering information	2
6.	Limiting values	3
7.	Thermal characteristics	5
8.	Characteristics	6
9.	Package outline	8
10.	Legal information	9

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